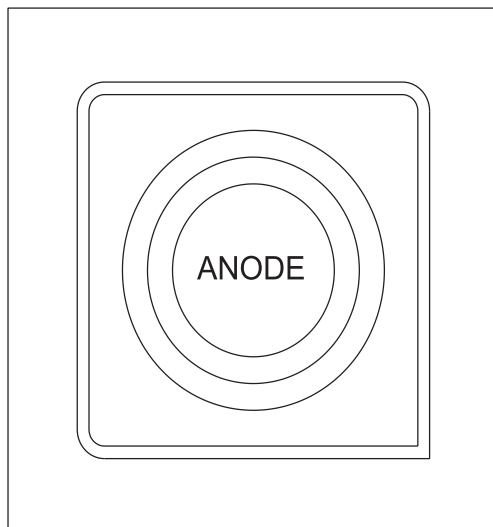


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	9.0 x 9.0 MILS
Die Thickness	7.9 MILS
Anode Bonding Pad Area	4.8 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY

BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

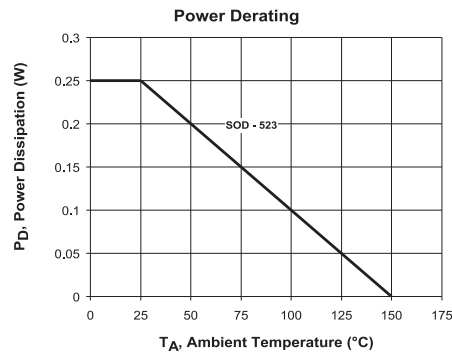
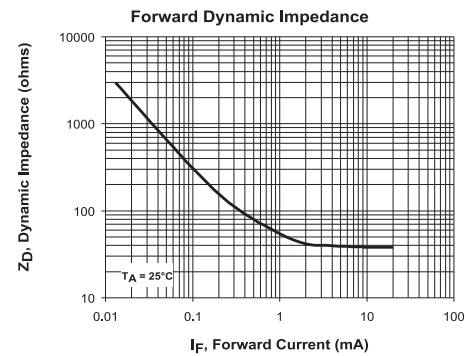
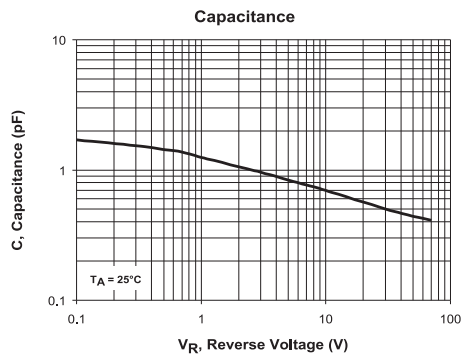
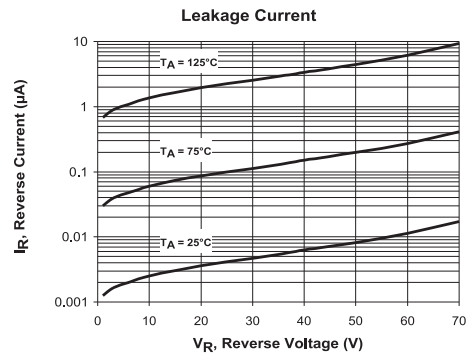
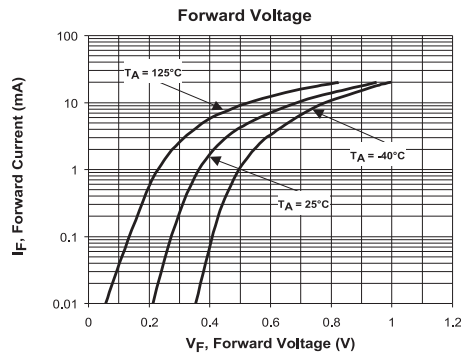
139,050

PRINCIPAL DEVICE TYPES

CMDD6263
CMKD6263
CMOD6263
CMPD6263 SERIES
CMSD6263 SERIES
1N6263

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R1 (1-August 2002)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R1 (1-August 2002)